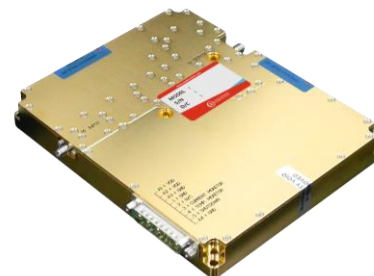


AMP3060-1 SOLID STATE HIGH POWER AMPLIFIER

FEATURES

Class AB linear GaAsFET design
Instantaneous wide bandwidth
Suitable for all single channel modulation standards
Built-in protection circuits
High reliability and ruggedness



ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	38 - 40 GHz	
Power Output @ P1 dB	7 Watt Min	CW
Power Gain	40 dB Min	
Power Gain Flatness	3.0 dB p-p Max	Constant input power
Input / Output Return Loss	-10 dB Max	Relative to 50 Ohm
Harmonics	<-30 dBc Typ	At rated Pout
Spurious	-60 dBc Max	Non-harmonics
Operating Voltage	9.0 ± 0.1 VDC Nom	Idq = 22 Amp Typ
Current Consumption	36.0 Amp Max / 30 Amp Typ	At rated Pout
Input Power Protection	+0 dBm Max	<10 Sec without damage
Load VSWR Protection	3 : 1 Max	<1 minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +55 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	140 x 175 x 22 mm	Excluding connectors
Weight	1.1 Kg	
RF Connectors In/Out	2.92 mm K-Type	Optional WR28 Output
DC Power / Interface Connector	9-Pin Hybrid D-Sub	
Cooling	External Heatsink	Forced air required

D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1	N/C	Reserved
2	N/C	Reserved
3	CURRENT SENSOR	Id@10mV/100mA Typ
4	TEMP SENSOR	V _T @10mV/°C + 500mV Typ
5	SHUTDOWN	TTL
A1, A2	VDD	9VDC
A3, A4	GND	Ground

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OUTLINE DRAWING

